

Taiwan Semiconductor

1A, 50 - 1000V Surface Mount Rectifier

FEATURES

TAIWAN

- Plastic package has carries underwriters
- Ideal for automated placement

EMICONDUCTOR

- Surge overload rating to 30A peak
- Reliable low cost construction utilizing molded
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Inverters and Converters
- Free Wheeling diodes

MECHANICAL DATA

- Case: MELF
- Molding compound meets UL 94V-0 flammability rating
- Meet JESD 201 class 1A whisker test
- Polarity: Indicated by cathode band
- Weight: 120.00mg (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
١ _F	1	А	
V _{RRM}	50 - 1000	V	
I _{FSM}	30	А	
T _{J MAX}	150	°C	
Package	MELF		





MELF

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)									
PARAMETER	SYMBOL	LL4001	LL4002	LL4003	LL4004	LL4005	LL4006	LL4007	UNIT
	31 MIBUL	G	G	G	G	G	G	G	
Repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Reverse voltage, total rms value	V _{R(RMS)}	35	70	140	280	420	560	700	V
DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Forward current	I _F				1				Α
Surge peak forward current 8.3ms single half sine-wave superimposed on rated load	I _{FSM}				30				A
Junction temperature	T _J -65 to +150		°C						
Storage temperature	T _{STG}	T _{STG} -65 to +150			°C				



THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-case thermal resistance	R _{eJC}	50	°C/W	

ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	ТҮР	MAX	UNIT	
Forward voltage ⁽¹⁾	I _F = 1.0A	V _F	-	1.1	V	
Reverse current @ rated $V_R^{(2)}$	$T_J = 25^{\circ}C$		-	5	μA	
Reverse current @ rated v _R	T _J = 125°C	- I _R	-	100	μA	
Junction capacitance	1 MHz, V _R =4.0V	CJ	15	-	pF	

Notes:

1. Pulse test with PW=0.3 ms

2. Pulse test with PW=30 ms

ORDERING INFORMATION			
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING	
LL400xG L0G	MELF	5,000/13" reel	

Notes:

(1) "x" defines voltage from 50V(LL4001G) - 1000V(LL4007G)



CHARACTERISTICS CURVES (T_A = 25°C unless otherwise noted)

1.2 1 Average Forward Current (A) 0.8 0.6 0.4 0.2 Resistive or Inductive Load 0 25 100 0 50 75 125 150 Terminal Temperature (°C)

Fig.1 Forward Current Derating Curve

Fig.3 Typical Forward Characteristics



Fig.5 Typical Junction Capacitance



Fig.2 Maximum Non-Repetitive Peak Forward Surge Current



Fig.4 Typical Reverse Characteristics



Fig.6 Typical Transient Thermal Impedance





PACKAGE OUTLINE DIMENSIONS





	Unit	(mm)	Unit (inch)		
DIM	Min	Max	Min	Max	
А	4.80	5.50	0.189	0.217	
В	2.25	2.67	0.089	0.105	
С	0.30	0.60	0.012	0.024	

SUGGESTED PAD LAYOUT



DIM	Unit (mm)	Unit (inch)
DIIVI	ТҮР	ТҮР
С	4.80	0.189
G	3.30	0.130
Х	1.50	0.059
X1	6.30	0.248
Y	2.70	0.106



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